

Vishay Siliconix

P-Channel 30-V (D-S) MOSFET

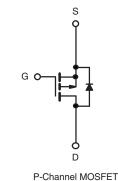
PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)		
- 30	0.0075 at V _{GS} = - 10 V	- 15		
	0.011 at V _{GS} = - 4.5 V	- 12.3		

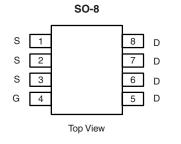


- Halogen-free According to IEC 61249-2-21
 Available
- TrenchFET[®] Power MOSFET

APPLICATIONS

- Notebook
 - Load Switch
 - Battery Switch





Ordering Information: Si4413ADY-T1-E3 (Lead (Pb)-free) Si4413ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \degree C$, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 30		V	
Gate-Source Voltage		V _{GS}	± 20			
	T _A = 25 °C	– I _D	- 15	- 10.5		
Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$	T _A = 70 °C		- 11.8	- 8.3	А	
Pulsed Drain Current		I _{DM}	- 50		А	
Continuous Source Current (Diode Conduction) ^a		۱ _s	- 2.7	- 1.36		
	T _A = 25 °C	PD	3.0	1.5	W	
Maximum Power Dissipation ^a	T _A = 70 °C	' D	1.9	0.95	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mauina lugation to Anabianta	t ≤ 10 s	R _{thJA}	33	42	
Maximum Junction-to-Ambient ^a	Steady State		70	84	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	16	21	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

HALOGEN

FREE

Available

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}				± 100	nA	
	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70 ^{\circ}\text{C}$			- 1	μΑ	
Zero Gate Voltage Drain Current					- 10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -10 V$	- 30			Α	
Drain-Source On-State Resistance ^a	Р	V _{GS} = - 10 V, I _D = - 13 A		0.0063	0.0075	0	
	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 10 A		0.0083	0.011	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -13 \text{ A}$		50		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = -2.7 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.74	- 1.1	V	
Dynamic ^b			•				
Total Gate Charge	Qg			61	95	nC	
Gate-Source Charge	Q _{gs}	V_{DS} = - 15 V, V_{GS} = - 5 V, I_{D} = - 13 A		15.5			
Gate-Drain Charge	Q _{gd}			32			
Turn-On Delay Time	t _{d(on)}			21	35		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		18	30	ns	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 10 V, R_G = 6 Ω		170	260		
Fall Time	t _f			97	150		
Gate Resistance	R _g		Ī	3.4		Ω	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.1 A, dl/dt = 100 A/μs		70	110	ns	

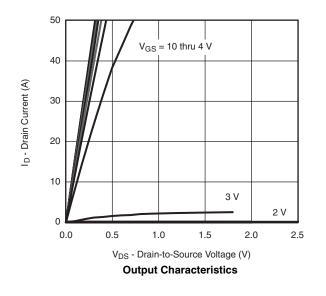
Notes:

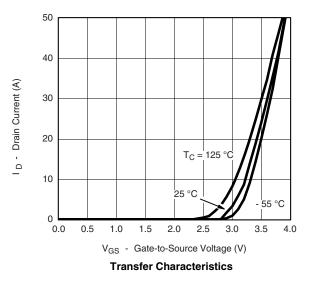
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

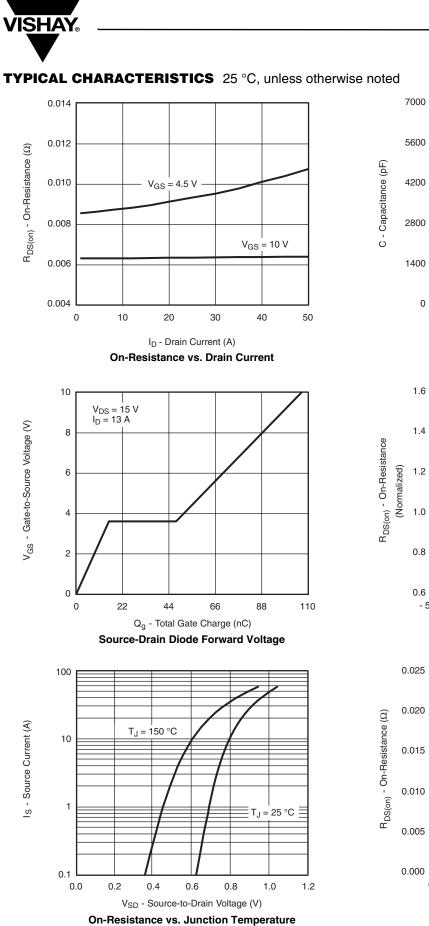
b. Guaranteed by design, not subject to production testing.

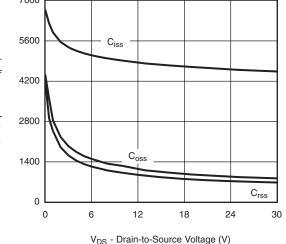
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





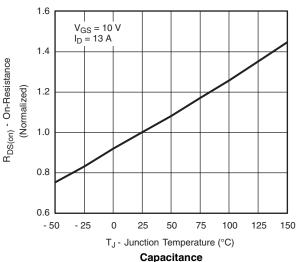


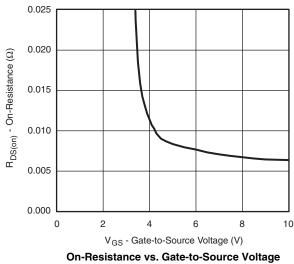


Si4413ADY

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Gate Charge



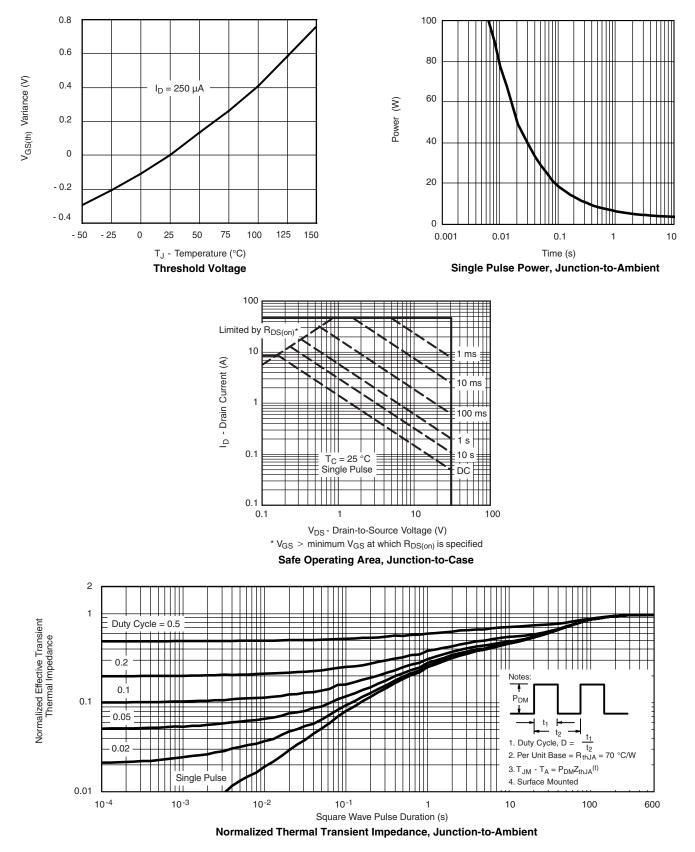


Document Number: 73792 S-83096-Rev. C, 29-Dec-08

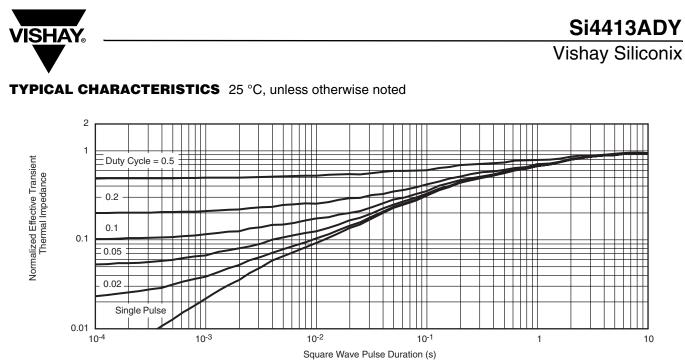
Si4413ADY

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73792.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





	MILLIM	IETERS	INC	HES		
DIM	Min	Мах	Min	Max		
A	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498						

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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